

In the Claims:

1. (Currently Amended) A metal-insulator-metal (MIM) capacitor plate, comprising:
 - a first conductive layer, the first conductive layer comprising a first material;
 - at least one thin conductive material layer disposed over the first conductive layer, the thin conductive material layer comprising a second material, the second material being different than the first material; and
 - at least one second conductive layer disposed over at least one of the at least one thin conductive material layers, wherein each of the first conductive layer, the at least one thin conductive layer and the at least one second conductive layer are electrically coupled together and wherein the first conductive layer, the at least one thin conductive layer and the at least one second conductive layer are each patterned to have outer edges that are aligned relative to one another.
2. (Original) The MIM capacitor plate according to Claim 1, wherein the at least one thin conductive material layer comprises TiN, TaN, or WN.
3. (Original) The MIM capacitor plate according to Claim 1, wherein the at least one thin conductive material layer comprises a thickness of about 450 Angstroms or less.
4. (Currently Amended) The A metal-insulator-metal (MIM) capacitor plate according to claim 1, comprising:
 - a first conductive layer, the first conductive layer comprising a first material;
 - at least one thin conductive material layer disposed over the first conductive layer, the thin conductive material layer comprising a second material, the second material being different

than the first material, wherein the at least one thin conductive material layer comprises [[:]] a first barrier layer disposed over the first conductive layer; and a conductive layer disposed over the first barrier layer; and

at least one second conductive layer disposed over at least one of the at least one thin conductive material layers.

5. (Original) The MIM capacitor plate according to Claim 4, wherein the first barrier layer comprises Ti, Ta or W, and wherein the conductive layer comprises TiN, TaN, or WN.

6. (Original) The MIM capacitor plate according to Claim 4, wherein the at least one thin conductive material layer further comprises a second barrier layer disposed over the conductive layer.

7. (Original) The MIM capacitor plate according to Claim 6, wherein the first barrier layer comprises Ti, Ta or W, wherein the conductive layer comprises TiN, TaN, or WN, and wherein the second barrier layer comprises Ti, Ta or W.

8. (Currently Amended) The A metal-insulator-metal (MIM) capacitor plate according to
claim 1, comprising:

a first conductive layer, the first conductive layer comprising a first material;
at least one thin conductive material layer disposed over the first conductive layer, the
thin conductive material layer comprising a second material, the second material being different
than the first material; and

at least one second conductive layer disposed over at least one of the at least one thin

conductive material layers, wherein the at least one second conductive layer comprises the first material.

9. (Original) The MIM capacitor plate according to Claim 1, wherein the first conductive layer and the at least one second conductive layer comprise Al.

10. (Original) The MIM capacitor plate according to Claim 1, wherein the MIM capacitor plate is formed in a metallization layer of a semiconductor device, the metallization layer comprising a plurality of conductive lines having a first thickness, wherein the MIM capacitor plate comprises the first thickness.

11. (Original) The MIM capacitor plate according to Claim 1, wherein the MIM capacitor plate comprises a bottom plate of a MIM capacitor.

12. (Original) The MIM capacitor plate according to Claim 1, wherein the MIM capacitor plate comprises a top plate of a MIM capacitor.

13. (Currently Amended) A metal-insulator-metal (MIM) capacitor, comprising:
a first plate;
a dielectric material disposed over the first plate; and
a second plate disposed over the dielectric material, wherein the first plate or the second plate comprises:

a first conductive layer, the first conductive layer comprising a first material;
at least one thin conductive material layer disposed over the first conductive layer, the at least
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one thin conductive material layer comprising a second material, the second material being different than the first material; and

at least one second conductive layer disposed over at least one of the at least one thin conductive material layers, wherein each of the first conductive layer, the at least one thin conductive layer and the at least one second conductive layer are electrically coupled together and wherein the first conductive layer, the at least one thin conductive layer and the at least one second conductive layer are each patterned to include outer edges that are aligned relative to one another.

14. (Original) The MIM capacitor according to Claim 13, wherein either the first plate or second plate is formed in a metallization layer of a semiconductor device, the metallization layer comprising a plurality of conductive lines having a first thickness, wherein the MIM capacitor first plate or second plate comprises the first thickness.

15. (Original) The MIM capacitor according to Claim 13, wherein the at least one thin conductive material layer comprises TiN, TaN, or WN.

16. (Original) The MIM capacitor according to Claim 15, wherein the at least one thin conductive material layer comprises a thickness of about 450 Angstroms or less.

17. (Original) The MIM capacitor according to Claim 13, wherein the at least one thin conductive material layer comprises:

a first barrier layer disposed over the first conductive layer; and
a conductive layer disposed over the first barrier layer.

18. (Original) The MIM capacitor according to Claim 17, wherein the first barrier layer comprises Ti, Ta or W, and wherein the conductive layer comprises TiN, TaN, or WN.

19. (Original) The MIM capacitor according to Claim 17, wherein the at least one thin conductive material layer further comprises a second barrier layer disposed over the conductive layer.

20. (Original) The MIM capacitor according to Claim 19, wherein the first barrier layer comprises Ti, Ta or W, wherein the conductive layer comprises TiN, TaN, or WN, and wherein the second barrier layer comprises Ti, Ta or W.

21. (Original) The MIM capacitor according to Claim 13, wherein the first conductive layer and the at least one second conductive layer comprise the same material.

22. (Original) The MIM capacitor according to Claim 13, wherein the first conductive layer and the at least one second conductive layer comprise Al.

23. (Original) The MIM capacitor according to Claim 13, wherein the first plate comprises:
a first conductive layer, the first conductive layer comprising a first material;
at least one first thin conductive material layer disposed over the first conductive layer, the at least one first thin conductive material layer comprising a second material, the second material being different than the first material; and
at least one second conductive layer disposed over at least one of the at least one thin conductive material layers;

and wherein the second plate comprises:

 a third conductive layer disposed over the dielectric material, the third conductive layer comprising a third material;

 at least one second thin conductive material layer disposed over the third conductive layer, the at least one second thin conductive material layer comprising a fourth material, the fourth material being different than the third material; and

 at least one fourth conductive layer disposed over at least one of the at least one second thin conductive material layers.

24. (Original) The MIM capacitor according to Claim 23, wherein the first conductive layer, the at least one second conductive layer, the third conductive layer and the at least one fourth conductive layer comprise Al, and wherein the at least one first thin conductive material layer and the at least one second thin conductive material layer comprise about 450 Angstroms or less of TiN, TaN, or WN.

25. (Original) The MIM capacitor according to Claim 24, wherein the at least one first thin conductive material layer and the at least one second thin conductive material layer further comprise a barrier layer disposed over or under the TiN, TaN or WN.

26-40. (Canceled)

41. (New) The MIM capacitor plate according to Claim 8, wherein the first material comprises aluminum.

42. (New) The MIM capacitor plate according to Claim 41, wherein the second material is selected from the group consisting of TiN, TaN and WN.

43. (New) A metal-insulator-metal (MIM) capacitor comprising:

a first conductive plate comprising a first layer of aluminum and a second layer of aluminum separated by a layer of conductive material, the conductive material comprising TiN,

TaN or WN;

a capacitor dielectric adjacent the first conductive plate; and

a second conductive plate adjacent the capacitor dielectric, wherein the first conductive plate, the capacitor dielectric and the second conductive plate form a capacitor.

44. (New) The MIM capacitor of claim 43, wherein the first conductive plate overlies the capacitor dielectric and wherein the capacitor dielectric overlies the second conductive plate.

45. (New) The MIM capacitor of claim 43, wherein the second conductive plate overlies the capacitor dielectric and wherein the capacitor dielectric overlies the first conductive plate.

46. (New) The MIM capacitor of claim 43, wherein the first conductive plate is formed within a metallization layer, the metallization layer further including a plurality of conductive lines, wherein the first conductive plate and the plurality of conductive lines each have a common thickness.

47. (New) The MIM capacitor of claim 43, wherein the layer of conductive material has a thickness of less than about 450Å.

48. (New) The MIM capacitor of claim 43, wherein the second conductive plate comprises a first layer of aluminum and a second layer of aluminum separated by a layer of conductive material, the conductive material comprising TiN, TaN or WN.